

ABSTRACT

ELECTRONIC DEVICE AND METHOD OF FABRICATING THE SAME

5 An electronic device includes a semiconductor memory
comprising row lines, column lines, memory cells, and a
plurality of contact plugs including row contact plugs
respectively coupled to the row lines and column contact
plugs respectively coupled to the column lines. Each memory
10 cell is coupled to a row line and a column line, and has a
current path comprising a portion of that row line and a
portion of that column line. First and second contact plug are
respectively coupled to first and second memory cells
respectively having first and second current paths. A
15 resistance of the first current path is lower than a resistance
of the second current path, and a resistance of the first
contact plug is increased relative to a resistance of the second
contact plug to offset the lower resistance of the first current
path.

20 FIG. 1C